

PowerMOS transistor**BUK436-1000B****GENERAL DESCRIPTION**

N-channel enhancement mode field-effect power transistor in a plastic envelope.

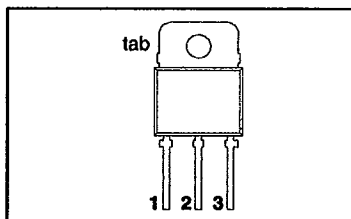
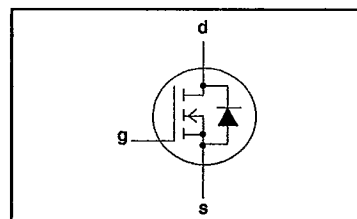
The device is intended for use in Switched Mode Power Supplies (SMPS), motor control, welding, DC/DC and AC/DC converters, and in general purpose switching applications.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{DS}	Drain-source voltage	1000	V
I_D	Drain current (DC)	3.1	A
P_{tot}	Total power dissipation	125	W
$R_{DS(ON)}$	Drain-source on-state resistance	5	Ω

PINNING - SOT93

PIN	DESCRIPTION
1	gate
2	drain
3	source
tab	drain

PIN CONFIGURATION**SYMBOL****LIMITING VALUES**

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{DS}	Drain-source voltage	-	-	1000	V
V_{DGR}	Drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	1000	V
$\pm V_{GS}$	Gate-source voltage	-	-	30	V
I_D	Drain current (DC)	$T_{mb} = 25^\circ\text{C}$	-	3.1	A
I_D	Drain current (DC)	$T_{mb} = 100^\circ\text{C}$	-	2.0	A
I_{DM}	Drain current (pulse peak value)	$T_{mb} = 25^\circ\text{C}$	-	12	A
P_{tot}	Total power dissipation	$T_{mb} = 25^\circ\text{C}$	-	125	W
T_{stg}	Storage temperature	-	-55	150	$^\circ\text{C}$
T_J	Junction Temperature	-	-	150	$^\circ\text{C}$

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th j-mb}$	Thermal resistance junction to mounting base		-	-	1.0	K/W
$R_{th j-a}$	Thermal resistance junction to ambient		-	45	-	K/W

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STATIC CHARACTERISTICS

 $T_{mb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}; I_D = 0.25\text{ mA}$	1000	-	-	V
$V_{GS(TH)}$	Gate threshold voltage	$V_{DS} = V_{GS}; I_D = 1\text{ mA}$	2.1	3.0	4.0	V
I_{DSS}	Zero gate voltage drain current	$V_{DS} = 1000\text{ V}; V_{GS} = 0\text{ V}; T_J = 25\text{ }^{\circ}\text{C}$	-	2	20	μA
I_{DSS}	Zero gate voltage drain current	$V_{DS} = 1000\text{ V}; V_{GS} = 0\text{ V}; T_J = 125\text{ }^{\circ}\text{C}$	-	0.1	1.0	mA
I_{GSS}	Gate source leakage current	$V_{GS} = \pm 30\text{ V}; V_{DS} = 0\text{ V}$	-	10	100	nA
$R_{DS(ON)}$	Drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 1.5\text{ A}$	-	4.5	5.0	Ω

DYNAMIC CHARACTERISTICS

 $T_{mb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
g_{fs}	Forward transconductance	$V_{DS} = 25\text{ V}; I_D = 1.5\text{ A}$	3.0	4.3	-	S
C_{iss}	Input capacitance	$V_{GS} = 0\text{ V}; V_{DS} = 25\text{ V}; f = 1\text{ MHz}$	-	1000	1250	pF
C_{oss}	Output capacitance		-	80	120	pF
C_{rss}	Feedback capacitance		-	30	50	pF
t_{don}	Turn-on delay time	$V_{DD} = 30\text{ V}; I_D = 2.3\text{ A};$	-	10	25	ns
t_r	Turn-on rise time	$V_{GS} = 10\text{ V}; R_{GS} = 50\text{ }\Omega;$	-	25	40	ns
t_{doff}	Turn-off delay time	$R_{gen} = 50\text{ }\Omega$	-	130	150	ns
t_f	Turn-off fall time		-	40	60	ns
L_d	Internal drain inductance	Measured from contact screw on tab to centre of die	-	5	-	nH
L_d	Internal drain inductance	Measured from drain lead 6 mm from package to centre of die	-	5	-	nH
L_s	Internal source inductance	Measured from source lead 6 mm from package to source bond pad	-	12.5	-	nH

REVERSE DIODE LIMITING VALUES AND CHARACTERISTICS

 $T_{mb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{DR}	Continuous reverse drain current	-	-	-	3.5	A
I_{DRM}	Pulsed reverse drain current	-	-	-	14	A
V_{SD}	Diode forward voltage	$I_F = 3.5\text{ A}; V_{GS} = 0\text{ V}$	-	1.0	1.3	V
t_r	Reverse recovery time	$I_F = 3.5\text{ A}; -di_F/dt = 100\text{ A}/\mu\text{s};$	-	1800	-	ns
Q_{rr}	Reverse recovery charge	$V_{GS} = 0\text{ V}; V_R = 100\text{ V}$	-	12	-	μC

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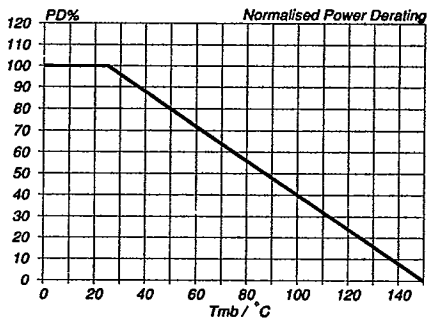


Fig.1. Normalised power dissipation.
 $PD\% = 100 \cdot P_D / P_{D\ 25\ ^\circ C} = f(T_{mb})$

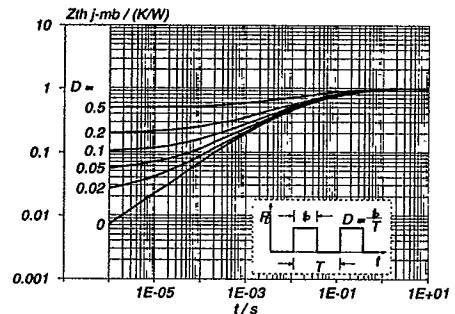


Fig.4. Transient thermal impedance.
 $Z_{th\ j-mb} = f(t)$; parameter $D = t_p / T$

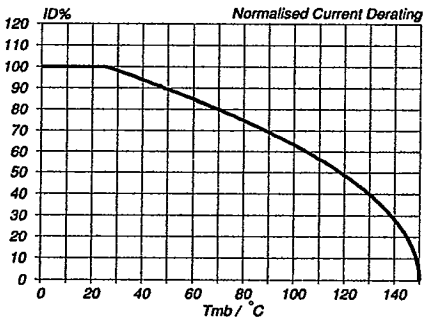


Fig.2. Normalised continuous drain current.
 $ID\% = 100 \cdot I_D / I_{D\ 25\ ^\circ C} = f(T_{mb})$; conditions: $V_{GS} \geq 10\ V$

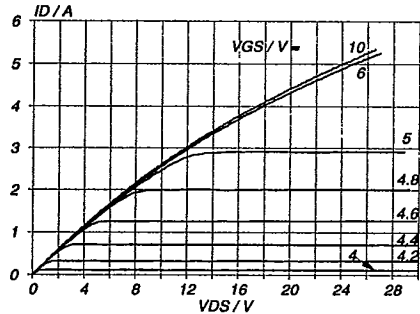


Fig.5. Typical output characteristics, $T_j = 25\ ^\circ C$.
 $I_D = f(V_{DS})$; parameter V_{GS}

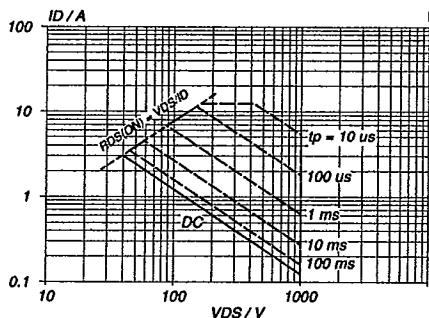


Fig.3. Safe operating area. $T_{mb} = 25\ ^\circ C$.
 $I_D \ \& \ I_{DM} = f(V_{DS})$; I_{DM} single pulse; parameter t_p

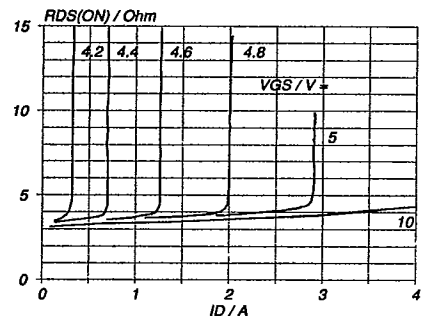


Fig.6. Typical on-state resistance, $T_j = 25\ ^\circ C$.
 $R_{DS(ON)} = f(I_D)$; parameter V_{GS}

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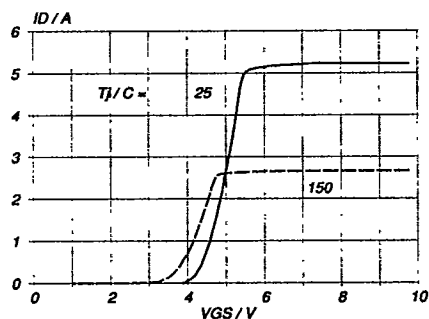


Fig. 7. Typical transfer characteristics.
 $I_D = f(V_{GS})$; conditions: $V_{DS} = 25 \text{ V}$; parameter T_j

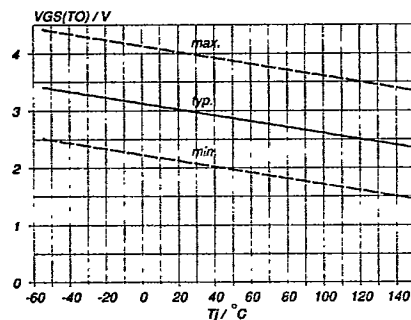


Fig. 10. Gate threshold voltage.
 $V_{GS(TO)} = f(T_j)$; conditions: $I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$

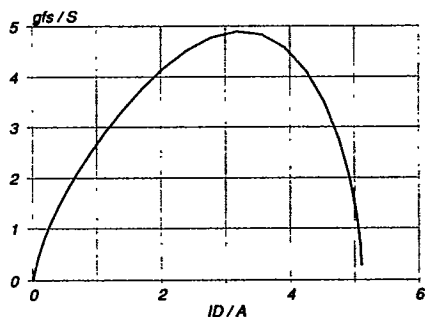


Fig. 8. Typical transconductance, $T_j = 25 \text{ °C}$.
 $g_{fs} = f(I_D)$; conditions: $V_{DS} = 25 \text{ V}$

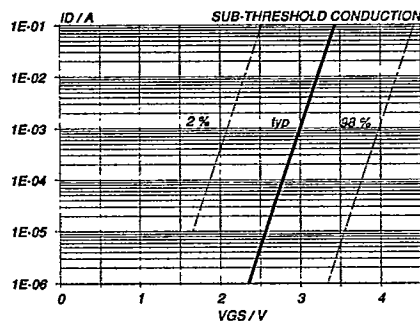


Fig. 11. Sub-threshold drain current.
 $I_D = f(V_{GS})$; conditions: $T_j = 25 \text{ °C}$; $V_{DS} = V_{GS}$

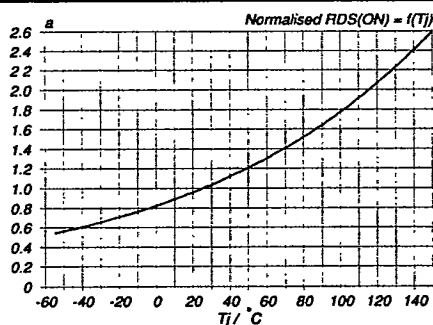


Fig. 9. Normalised drain-source on-state resistance.
 $a = R_{DS(ON)}/R_{DS(ON)25 \text{ °C}} = f(T_j)$; $I_D = 1.5 \text{ A}$; $V_{GS} = 10 \text{ V}$

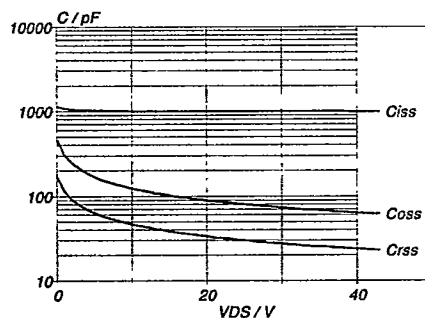


Fig. 12. Typical capacitances, C_{iss} , C_{oss} , C_{rss} .
 $C = f(V_{DS})$; conditions: $V_{GS} = 0 \text{ V}$; $f = 1 \text{ MHz}$

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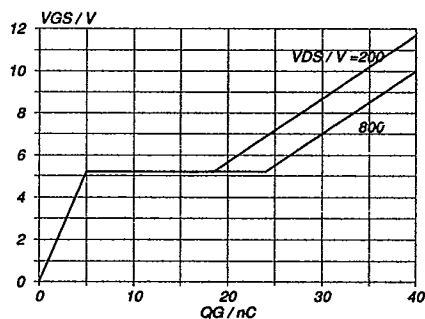


Fig. 13. Typical turn-on gate-charge characteristics. $V_{GS} = f(Q_G)$; conditions: $I_D = 3.5$ A; parameter V_{DS} .

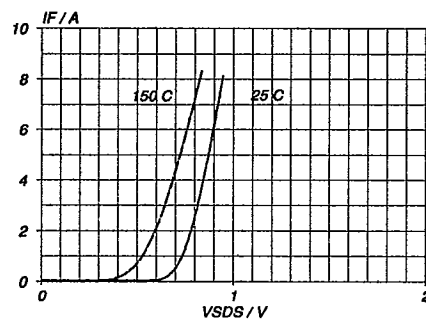


Fig. 14. Typical reverse diode current. $I_F = f(V_{SDS})$; conditions: $V_{GS} = 0$ V; parameter T_j .